



250V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C	
250V	8.5Ω @ V _{GS} = 10V	310mA	

Description and Applications

This 250V enhancement mode N-Channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of telecommunication and general high voltage circuits.

SOT89 and SOT23-6 versions are also available.

- Earth Recall and Dialing Switches
- Electronic Hook Switches
- High Voltage Power MOSFET Drivers
- Telecom Call Routers
- Solid State Relays

Features and Benefits

- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Complementary P-Channel Type ZVP4525G
- SOT223 Package
- Lead-Free Finish; RoHS Compliant (Notes 1& 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

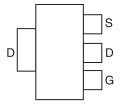
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.112 grams (Approximate)

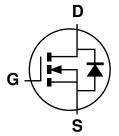




Top View



Pin Out Top-View



Equivalent Circuit

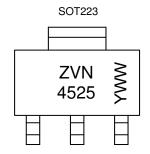
Ordering Information (Note 4)

Part Number	REEL SIZE (inches)	TAPE WIDTH (mm)	Packaging
ZVN4525GTA	7	8mm Embossed	1,000
ZVN4525GTC	13	8mm Embossed	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZVN 4525 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	250	V
Gate-Source Voltage		V _{GS}	±40	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25 ^{\circ}C$ $T_A = +70 ^{\circ}C$	I _D	310 248	mA
Pulsed Drain Current (Note 7)		Ірм	1.44	A
Continuous Source Current (Body Diode)		Is	1.1	Α
Pulsed Source Current (Body Diode)		I _{SM}	1.44	Α

Thermal Characteristics (@T_A = +25 ℃, unless otherwise specified.)

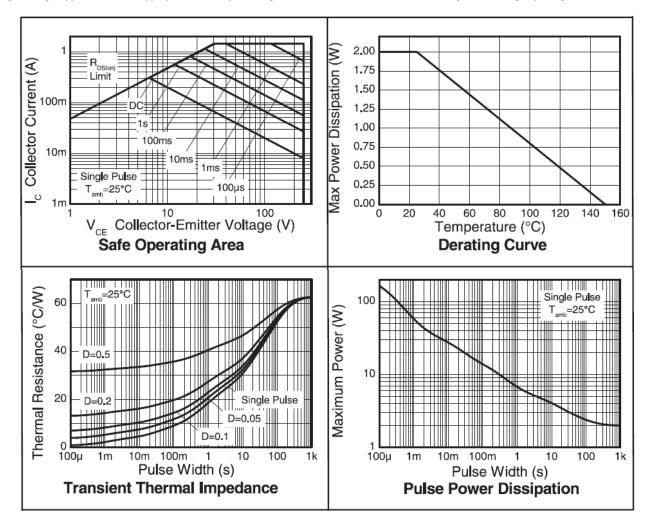
Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25 ℃ (Note 5) Linear Derating Factor	P _D	2 16	W mW/℃
Junction to Ambient (Note 5)	R _{0JA}	63	°C/W
Junction to Ambient (Note 6)	R _{0JA}	26	.C\M
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	∞

Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR4 PCB measured at t ≤ 5 seconds.

NB High Voltage Applications

For high voltage applications, the appropriate industry sector guidelines should be considered with regard to voltage spacing between conductors.



^{7.} Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal.



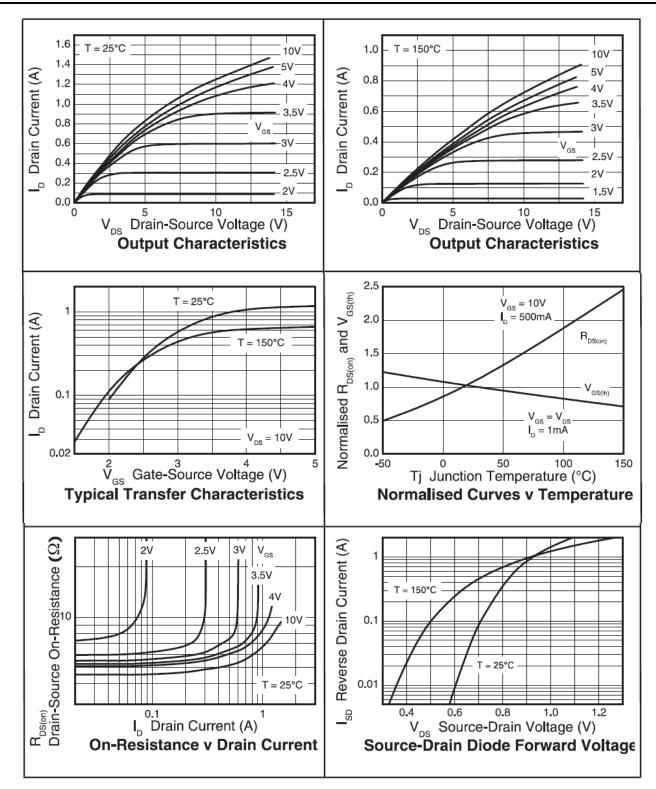
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	250	285	_	V	$I_D = 1mA$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}		35	500	nA	V _{DS} = 250V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	_	±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	0.8	1.4	1.8	V	$I_D = 1mA$, $V_{DS} = V_{GS}$	
On-State Drain Current (Note 8)	$I_{D(on)}$	3	_	_	Α	V _{DS} = 25V, V _{GS} = 10V	
		l	5.6	8.5	Ω	$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-State Resistance (Note 8)	R _{DS} (ON)	I	5.9	9		$V_{GS} = 4.5V, I_D = 360mA$	
			6.4	9.5		$V_{GS} = 2.5V, I_D = 20mA$	
Forward Transconductance (Note 10)	g _{fs}	0.3	0.475		S	$V_{DS} = 10V, I_D = 0.3A$	
Diode Forward Voltage (Note 8)	V _{SD}		_	0.97	V	$I_S = 360 \text{mA}, V_{GS} = 0 \text{V},$ $T_J = +25 \text{°C}$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		72	l	pF	V _{DS} = 25 V, V _{GS} = 0V -f = 1MHz	
Output Capacitance	Coss		11	l	pF		
Reverse Transfer Capacitance	Crss		3.6		рF		
Total Gate Charge	Q_{g}	1	2.6	3.65		VDS = 25V, VGS = 10V, ID = 360mA (refer to test circuit)	
Gate-Source Charge	Q_{gs}	l	0.2	0.28	nC		
Gate-Drain Charge	Q_{gd}	I	0.5	0.70			
Turn-On Delay Time (Note 9)	t _{d(on)}		1.25	l		V_{DD} = 30V, I_D = 360mA, R_G = 50 Ω , V_{GS} = 10V (refer to test circuit)	
Rise Time (Note 9)	t _r	l	1.7	l	no		
Turn-Off Delay Time (Note 9)	t _{d(off)}	l	11.4	-	ns		
Fall Time (Note 9)	t _f	l	3.5	-		lost offourt)	
Reverse Recovery Time	t _{rr}	l	186	260	ns	IF = 360mA, di/dt = 100A/μs,	
Reverse Recovery Charge	Q _{rr}	_	34	48	nC	TJ = +25℃	

Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

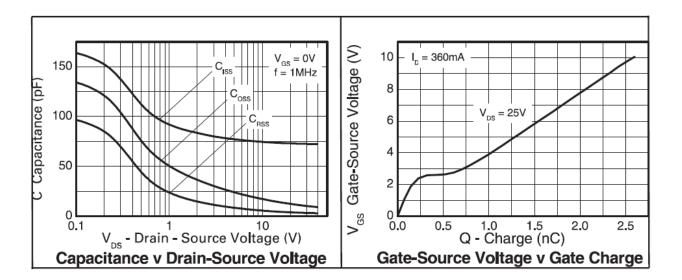


Typical Characteristics





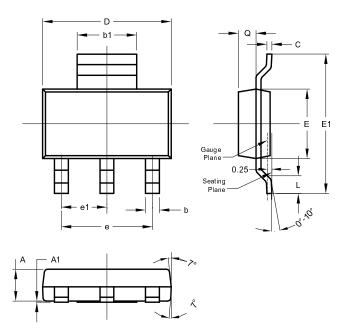
Typical Characteristics (cont.)





Package Outline Dimensions

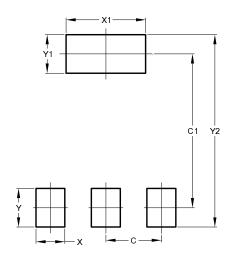
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
E	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
C2	8 00



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